Ordering number : EN5860A

Red Laser Diode

DL-3148-033

Index Guided AlGaInP Laser Diode

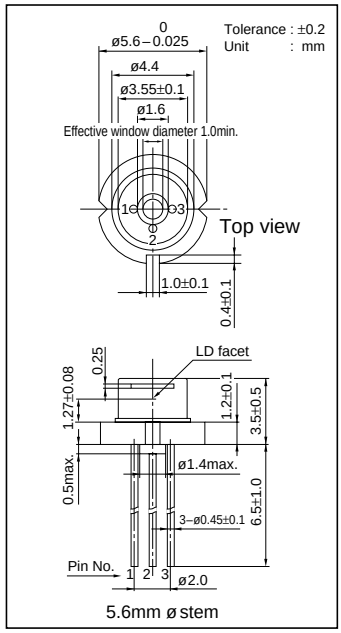
Overview

The DL-3148-033 is index guided 635 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and short wavelength are achieved by a strained multiple quantum well active layer. The lasing wavelength is 635nm which is 8 times brighter than that of 670nm lasers. The DL-3148-033 is suitable for applications such as bar-code scanners, laser printer, and other optical information systems.

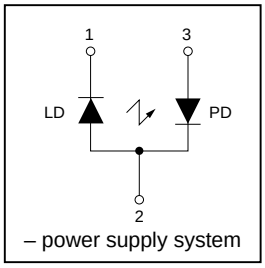
Features

- •Short wavelength : 635 nm (Typ.)
- •Low threshold current : Ith = 40 mA (Typ.)
- •High operating temperature : 5 mW at 50°C
- •Small package : 5.6 mmØ

Package Dimensions



Electrical Connection



Absolute Maximum Ratings at Tc=25°C

Parameter		Symbol	Ratings	Unit
Light Output		Po	5	mW
Reverse Voltage	Laser	VR	2	V
	PIN		30	
Operating Temperature		Topr	−10 to +50	°C
Storage Temperature		Tstg	−40 to +85	°C

Electrical and Optical Characteristics at Tc=25°C

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current		Ith	CW	–	40	60	mA
Operating Current		Iop	Po=5mW	–	55	75	mA
Operating Voltage		Vop	Po=5mW	–	2.2	2.4	V
Lasing Wavelength		λp	Po=5mW	–	635	640	nm
Beam ❋) Divergence	Perpendicular	θ⊥	Po=5mW	25	35	40	deg.
	Parallel	θ//	Po=5mW	6	8	10	deg.
Off Axis Angle	Perpendicular	Δθ⊥	–	–	–	±3	deg.
	Parallel	Δθ//	–	–	–	±3	deg.
Differential Efficiency		dPo/dIop	–	–	0.4	–	mW/mA
Monitoring Output Current		Im	Po=5mW	0.1	0.2	0.5	mA
Astigmatism		As	Po=5mW	–	8	–	μm

❋) Full angle at half maximum note : The above product specifications are subject to change without notice.

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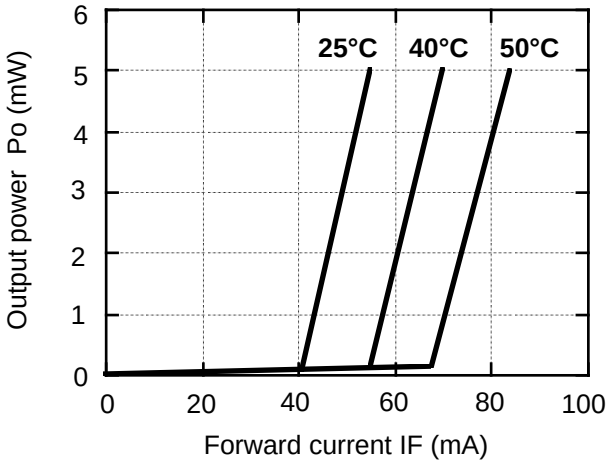
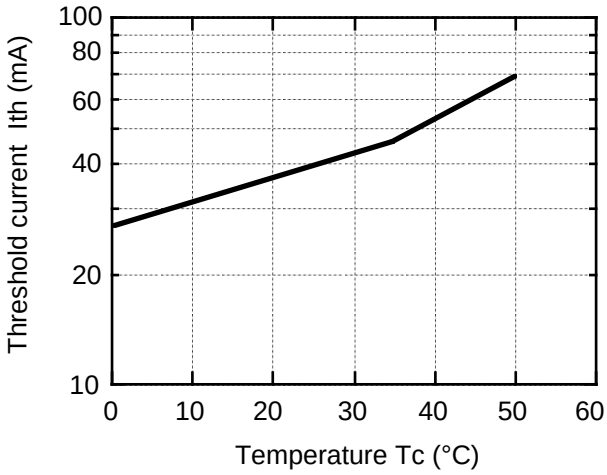
Characteristics

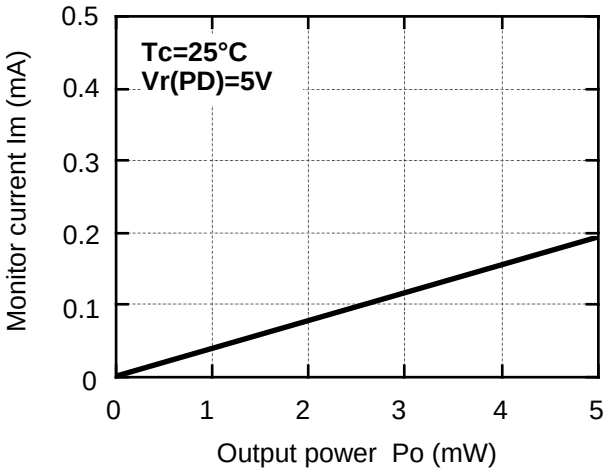
Output power vs. Forward current



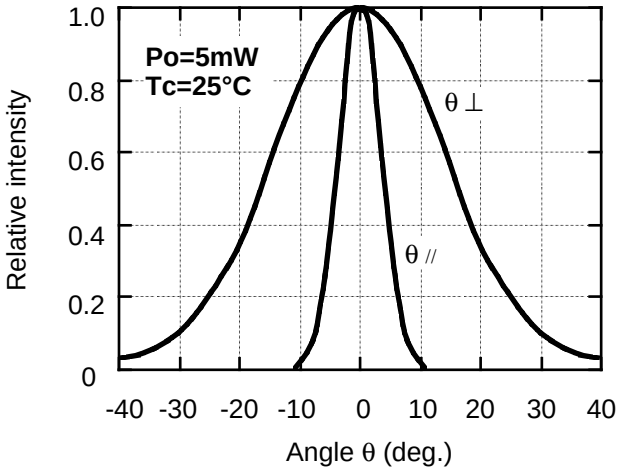
Threshold current vs. Temperature



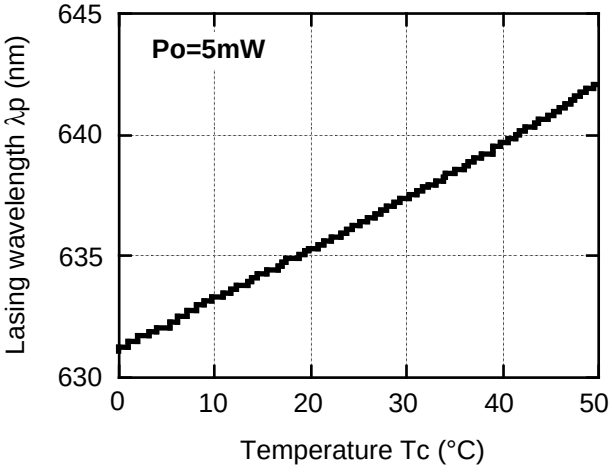
Monitor current vs. Output power



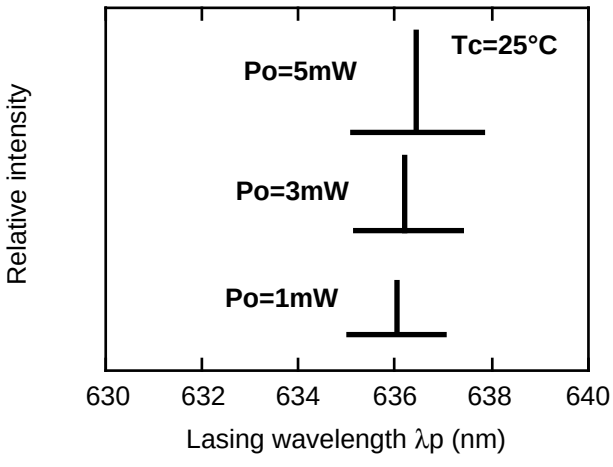
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



⚠ CAUTION

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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